

DERWENT-ACC-NO: 1993-149850

DERWENT-WEEK: 199318

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TITLE: Dielectric material for increasing
capacitance of capacitor of semiconductor device -
comprises mixed strontium barium titanate and has
high dielectric constant at room temp.

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PATENT-ASSIGNEE: SAMSUNG ELECTRONICS CO[SMSU]

PRIORITY-DATA: 1990KR-0005356 (April 17, 1990)

PATENT-FAMILY:

PUB-NO	PAGES	PUB-DATE	MAIN-IPC
KR 9206732 B		August 17, 1992	N/A
.000	H01G 004/12		

APPLICATION-DATA:

PUB-NO	APPL-DATE	APPL-DESCRIPTOR	APPL-NO
KR 9206732B		N/A	
1990KR-0005356		April 17, 1990	

INT-CL (IPC): H01G004/12

ABSTRACTED-PUB-NO: KR 9206732B

BASIC-ABSTRACT:

The dielectric substance for semiconductor device has
compsn. of formula $\text{Sr}(1-x)\text{Ba}(x)\text{TiO}_3$ (where $x = 0$ to 0.3). The dielectric
substance can undergo
phase transition without any change in crystal structure at
a temp. lower than
room temp. and has high dielectric constant at room temp.

The stoichiometric
ratio of the dielectric substance compsn. is easily
adjusted since the elements
Sr, Ba and Ti are not vapourised. The dielectric substance
is used to increase
the capacitance of capacitor of semiconductor device.

DERWENT-CLASS: L03 U11 V01 X12

CPI-CODES: L03-B03E;

EPI-CODES: U11-A08A2; V01-B03A1; X12-E01A;